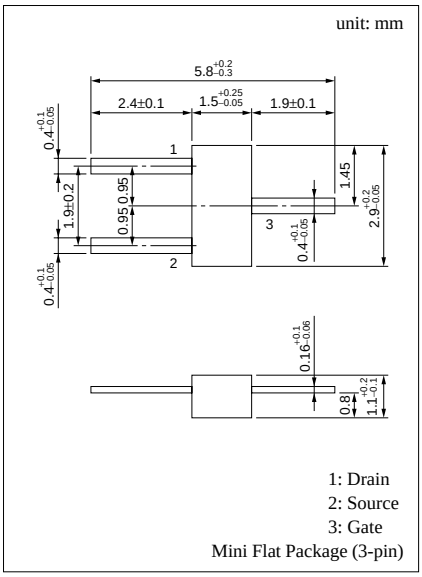
2SK123

Silicon N-Channel Junction FET

For impedance conversion in low frequency
For electret capacitor microphone

■ Features

- High mutual conductance g_m
- Low noise voltage of NV



Marking Symbol: 1H

Note: For the forming type, (Y) is indicated after the part No.

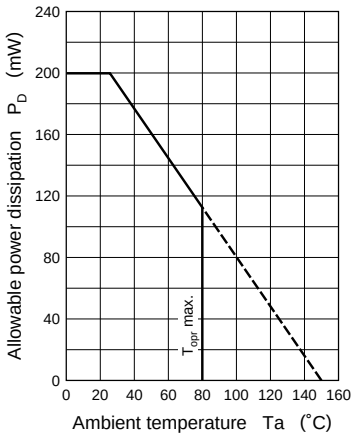
■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSO}	20	V
Drain to Gate voltage	V_{DGO}	20	V
Drain to Source current	I_{DSO}	2	mA
Drain to Gate current	I_{DGO}	2	mA
Gate to Source current	I_{GSO}	2	mA
Allowable power dissipation	P_D	200	mW
Operating ambient temperature	T_{opr}	−20 to +80	°C
Storage temperature	T_{stg}	−55 to +150	°C

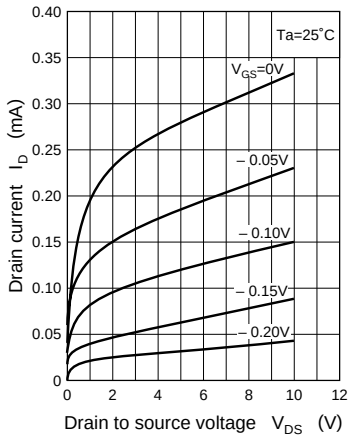
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Current consumption	I_D	V_D = 4.5V, C_O = 10pF, R_D = 2.2kΩ ± 1%	100		600	µA
Drain to Source cut-off current	I_{DSS}	V_{DS} = 4.5V, V_{GS} = 0	95		480	µA
Mutual conductance	g_m	V_D = 4.5V, V_{GS} = 0, f = 1kHz	0.7	1.6		mS
Noise figure	NV	V_D = 4.5V, R_D = 2.2kΩ ± 1% C_O = 10pF, A-curve			4	µV
Voltage gain	G_{V1}	V_D = 4.5V, R_D = 2.2kΩ ± 1% C_O = 10pF, e_G = 10mV, f = 1kHz	−3	2		dB
	G_{V2}	V_D = 12V, R_D = 2.2kΩ ± 1% C_O = 10pF, e_G = 10mV, f = 1kHz	0	3.3		dB
	G_{V3}	V_D = 1.5V, R_D = 2.2kΩ ± 1% C_O = 10pF, e_G = 10mV, f = 1kHz	−4.5	− 0.3		dB
Voltage gain difference	$\Delta\lvert G_{V2} - G_{V1}\rvert$		0		+3.5	dB
	$\Delta\lvert G_{V1} - G_{V3}\rvert$		0		+3.5	dB

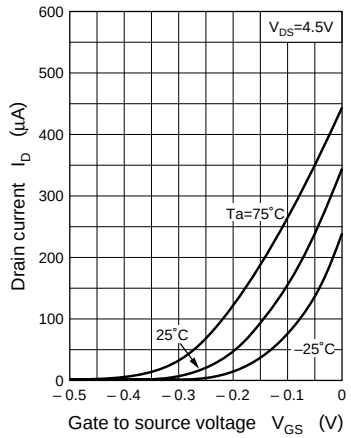
P_D — Ta



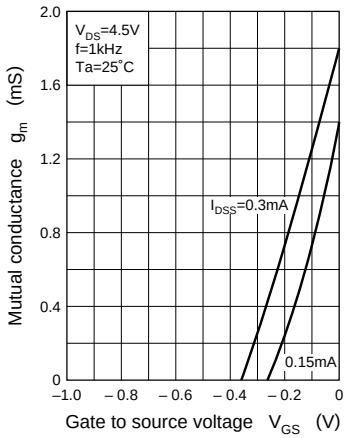
I_D — V_{DS}



I_D — V_{GS}



g_m — V_{GS}



g_m — I_D

